

wherein the thermoplastic material has thermoplastic properties and a thermal expansion coefficient of  $6.0 \times 10^{-5}$  [1/ $^{\circ}$ C] or less at a temperature of 80 $^{\circ}$ C to 130 $^{\circ}$ C.

22. (New) A thermoplastic material according to claim 21, wherein a line expansion coefficient is  $4.75 \times 10^{-5}$  [1/ $^{\circ}$ C] or less at a temperature of 150 $^{\circ}$ C to 200 $^{\circ}$ C.

23. (New) A thermoplastic material according to claim 21, wherein a line expansion coefficient ratio between a flow direction and a normal direction of the flow direction is 0.55 or more.

24. (New) A thermoplastic material according to claim 21, wherein the thermoplastic material has a bending strength after solidification of 74 MPa or more.

25. (New) A thermoplastic material according to claim 21, wherein an adhesion imparting agent is added to improve adhesion properties to another material by binding with a polar group.

26. (New) A thermoplastic material according to claim 21, further containing silica particles.

27. (New) A thermoplastic material according to claim 21, wherein the thermoplastic material is substantially free of fibrous material.

28. (New) A thermoplastic material according to claim 21, wherein the thermoplastic material is substantially free of thermosetting material.

*10 cm*

29. (New) A thermoplastic material according to claim 21, wherein a product obtained by multiplying a value of a line expansion at 25 to 80°C plus a line expansion at 80 to 125°C after solidification, by a bending strength is 25 MPa or less.

*29?*

30. (New) A thermoplastic material for sealing a semiconductor element, wherein the thermoplastic material has thermoplastic properties and a thermal expansion coefficient of  $6.0 \times 10^{-5}$  [1/°C] or less at a temperature of 80°C to 130°C.

31. (New) A process for manufacturing a semiconductor device comprising:  
electrically interconnecting a semiconductor element with one end of a  
conducting material; and  
sealing the semiconductor element and the one end of the conducting material  
with a thermoplastic material according to claim 21.

32. (New) A process for manufacturing a semiconductor device comprising:  
electrically interconnecting a semiconductor element with one end of a  
conducting material; and  
sealing the semiconductor element and the one end of the conducting material  
with a thermoplastic material according to claim 30.--

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**REMARKS**

Applicants submit this Preliminary Amendment of this continuation application  
under 37 C.F.R. 1.53(b) and request its entry prior to examination.